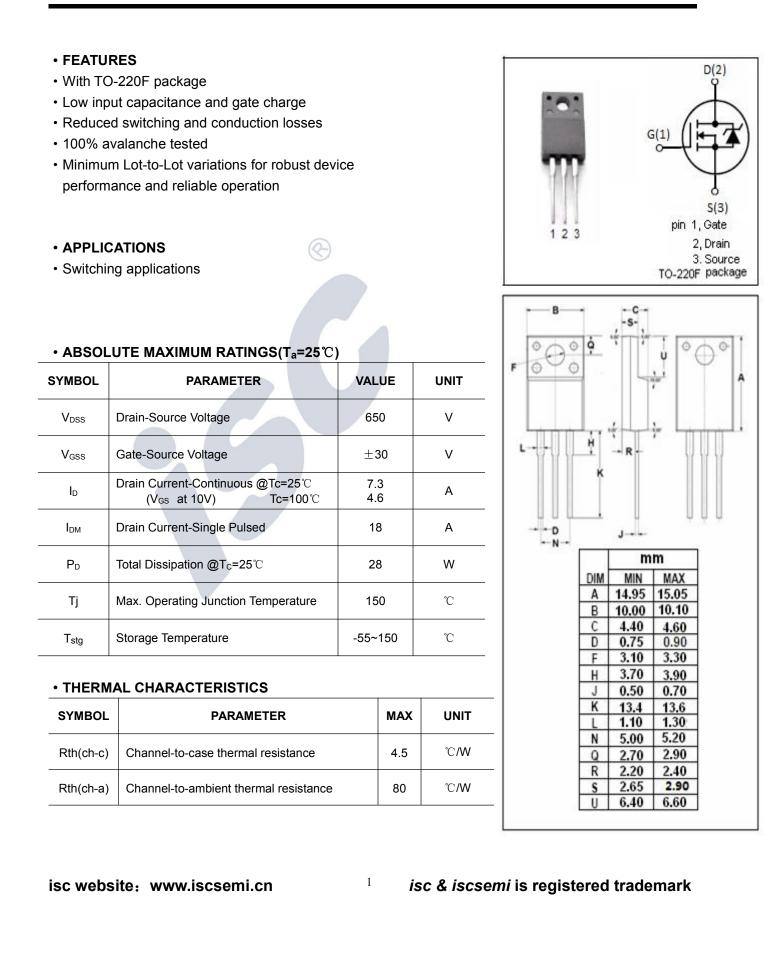


#### INCHANGE SEMICONDUCTOR

## **Isc N-Channel MOSFET Transistor**

## IPA65R600C6





# **Isc N-Channel MOSFET Transistor**

# IPA65R600C6

#### **ELECTRICAL CHARACTERISTICS**

#### $T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =1mA	650			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =0.21mA	2.5		3.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =2.1A		540	600	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V;V <sub>DS</sub> = 0V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0V;Tj=25℃ V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0V; Tj=150℃			1 100	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =3.2A, V <sub>GS</sub> = 0V		0.9		V

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